

SOT-23 Plastic-Encapsulate

型号：MMBD914

SWITCHING DIODE

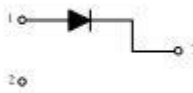
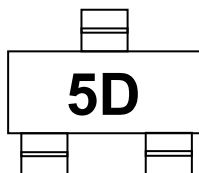
主要特性/Features

速度快，导通电压低 Fast speed, low on voltage

应用/Application

消费类电子产品

印字/MARKING 等效电路/Equivalent Circuit





极限参数/Absolute Maximum Ratings(TA=25°C unless otherwise noted)

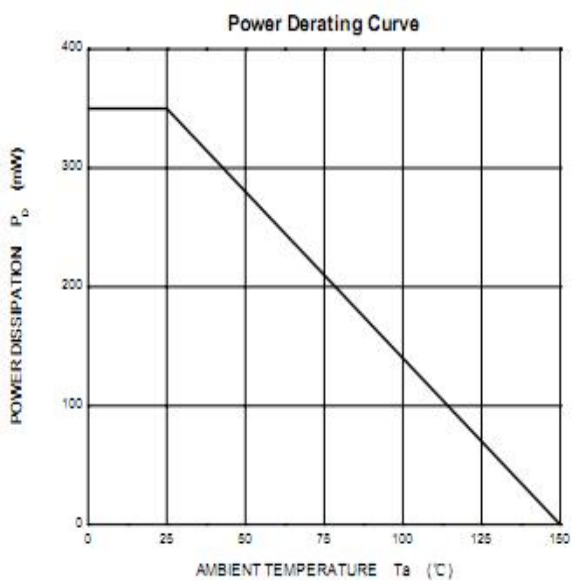
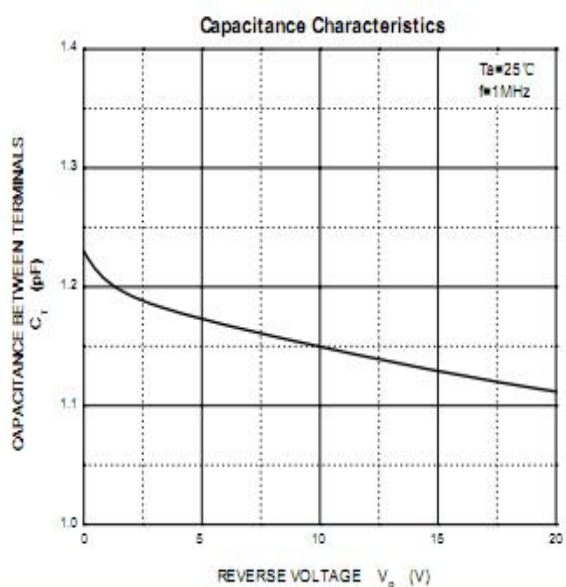
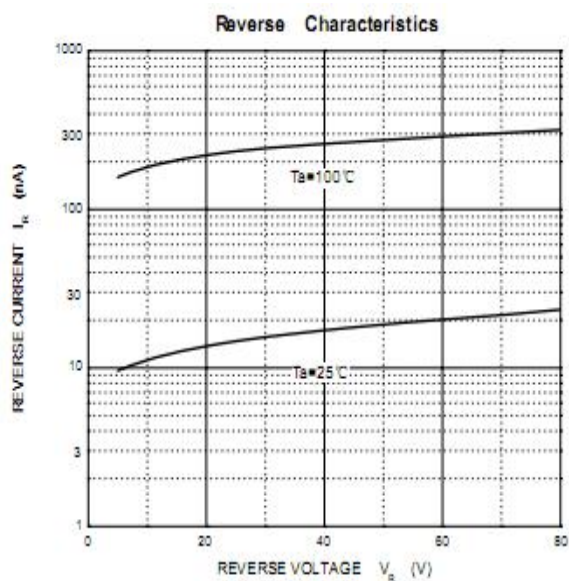
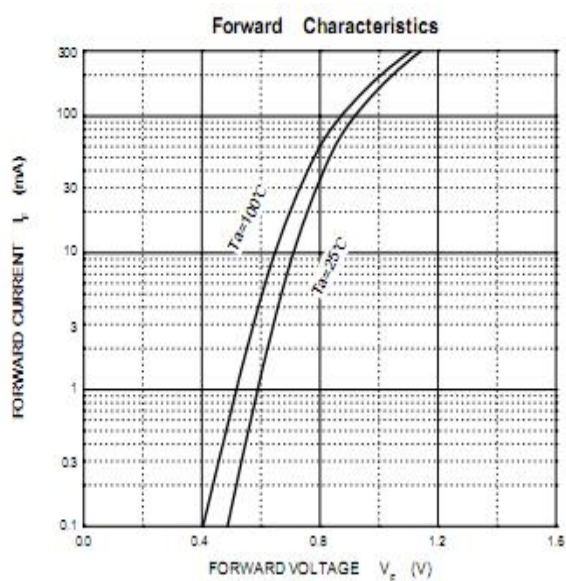
参数/Parameter	符号/ Symbol	数值 /Value	单位 /Unit
不可重复反向峰值电压 Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
反向峰值电压/Peak Repetitive Peak Reverse Voltage 反向工作电压/Working Peak Reverse Voltage 直流阻断电压/DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
平均整流输出电流/Average Rectified Output Current	I_O	300	mA
正向瞬时峰值电流/Peak forward surge Current	I_{FSM}	0.5	A
功率/ Power Dissipation	P_D	0.35	W
热阻/Thermal resistance junction to ambient air	$R_{\theta JA}$	375	°C/W
结温/Junction Temperature	T_j	150	°C
储存温度/ Storage Temperature	T_{stg}	-55 ~ 150	°C

电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

参数/Parameter	符号	测试条件	最小值	最大值	单位
反向击穿电压/Reverse Breakdown Voltage	$V_{R(BR)}$	$I_R=100\mu A$	100		V
正向电压/Forward Voltage	V_{F1}	$I_F=1mA$		0.715	V
	V_{F2}	$I_F=10mA$		0.855	V
	V_{F3}	$I_F=50mA$		1.0	V
	V_{F4}	$I_F=150mA$		1.25	V
反向漏电流/Reverse Current	I_{R1}	$V_R=75V$		1	μA
	I_{R2}	$V_R=20V$		25	nA
端电容/Capacitance Between Terminals	C_T	$V_R=0V, f=1MHz$		2	pF
反向恢复时间/Reverse Recovery Time	t_{rr}	$I_F=I_R=10mA,$ $I_{rr}=0.1 \times I_R$		4	nS

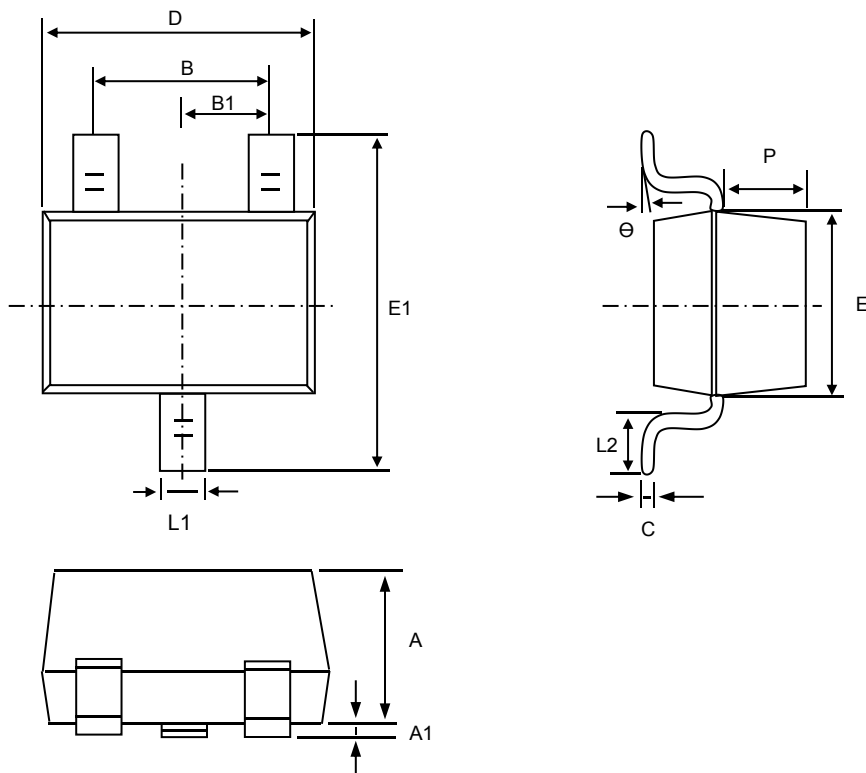


典型特性曲线图/Typical Characteristics





成品外观尺寸/SOT-23 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950TPY.		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600